Silicon Services

- Downsizing
- Laser marking
- Crystal reclaim
- Silicon Ingot
- Surface preparation
- Polishing
- Slicing
- Dicing
- Edge rounding
From ingots, blocks or wafers, we offer a variety of processes.

We propose a large variety of surface finishing for your materials:
• Lapping, back-grinding, single side or double side polishing
• High level finishing for special application
  (ex: “Epiready” finishing for electrochemical growth)
• Special treatment for bonding

SIL’TRONIX ST is specialized in silicon crystal growth and wafer manufacturing.

Our extensive know-how and our facilities are able to provide customized services on your material or CZ crystals grown on demand.

**CZ SPECIFIC INGOT**
- Orientation (100) or (111)
- Dopant: P-Boron or N-Phosphorus
- From conductive materials to 1 mOhm.cm
- Undoped: no added dopant

**MACHINING - DICING - SLICING**
- From ingots, blocks or wafers, we offer a variety of processes to shape your material:
  - Crystal or flat orientation
  - Shaping wafers into (pseudo) squares
  - Slicing with diamond inner diameter saw (ID)
  - Dicing (minimum size: 1.5 mm x 1.5 mm)

**POLISHING - RECLAIM**
- From ingots, blocks or wafers, we offer a variety of processes.
  We propose a large variety of surface finishing for your materials:
    • Lapping, back-grinding, single side or double side polishing
    • High level finishing for special application
      (ex: “Epiready” finishing for electrochemical growth)
    • Special treatment for bonding

SIL’TRONIX ST can reclaim your wafers. Depending on layer deposition, marks or defects on surface, we adjust our reclaim steps to offer you recycled wafers for a fraction of the cost of prime wafers.

**DOWNSIZING - EDGE GRINDING**
- Downsizing wafers or SOI wafers by laser cutting (ie: 6” -> 3x2”)
- Round, flat, edge grinding
- Specific edge profile (ie, angle at 45°…)

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